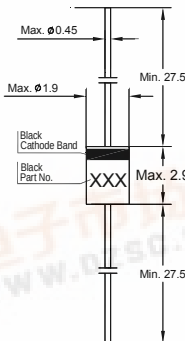


Silicon Epitaxial Planar Schottky Barrier Diode

Applications

- High speed switching circuit
- Small current rectification



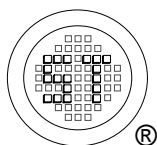
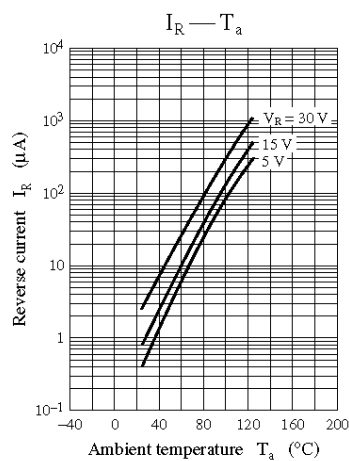
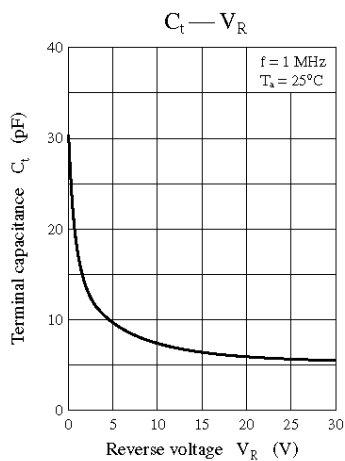
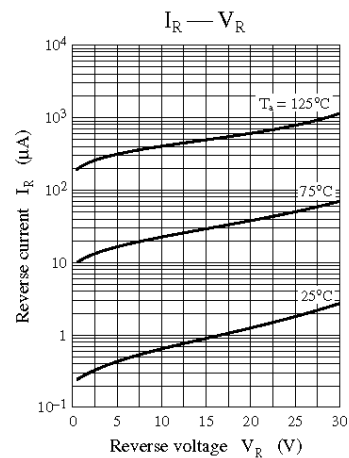
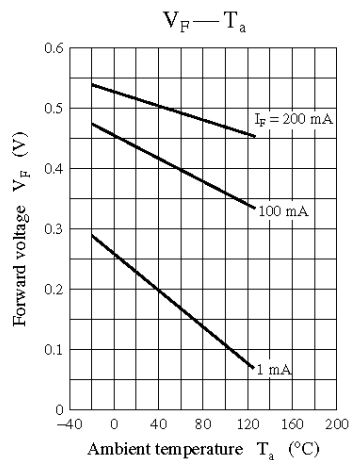
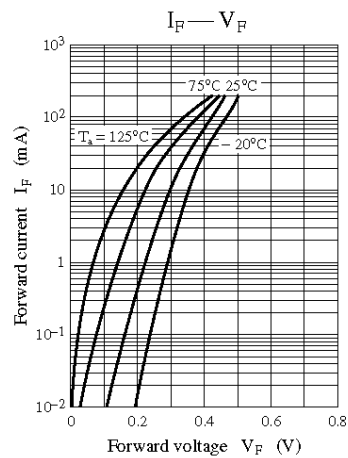
Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current (10 ms)	I_{FSM}	1.5	A
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

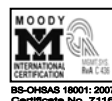
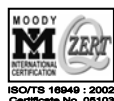
Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	-	0.6	V
Reverse Current at $V_R = 30\text{ V}$	I_R	-	50	μA
Capacitance between Terminals at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	30	-	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$, $i_{rr} = 0.25 I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	2	ns



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 23/07/2009